

*Full Length Research Paper*

# Low temperature synthesis of $\text{La}_2\text{O}_3$ and $\text{CrO}_2$ by Sol – Gel process

A. Bahari<sup>1\*</sup>, A. Anasari<sup>2</sup> and Z. Rahmani<sup>3</sup>

<sup>1</sup>Department of Physics, University of Mazandaran, Babolsar, Iran.

<sup>2</sup>Department of Physics, Islamic Azad University, Sari Branch, Sari, Iran.

<sup>3</sup>Department of Physics, Islamic Azad University, Central Tehran Branch, Iran.

Accepted 16 March, 2011

**Some issues such as tunneling, leakage current and light atom penetration through the film are threatening the ultra thin  $\text{SiO}_2$  be as a good dielectric for future industrial and electronic devices and in ceramic technologies. A series of experiments to synthesis  $\text{La}_2\text{O}_3$  as well as  $\text{CrO}_2$  has been done at low temperature with using sol-gel method. The nano structural properties of  $\text{La}_2\text{O}_3/\text{CrO}_2$  equipped with 5 to 40 nm size are investigated. The obtained results show the potential of  $\text{La}_2\text{O}_3/\text{CrO}_2$  for not only for lowering the interface – state density, but also as a good dielectric for the future of nano electronic. These structures have been studied by using XRD (x ray diffraction) technique and X- powder method.**

**Key words:** Nano structures,  $\text{La}_2\text{O}_3$ , Gate dielectric, x-powder method and sol-gel method.

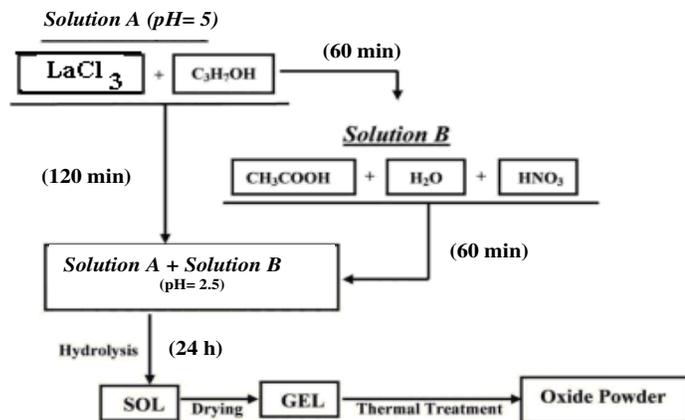
## INTRODUCTION

The gate  $\text{SiO}_2$  dielectric thickness in current complementary metal oxide semiconductor (CMOS) transistors is less than 1 nm. It is mostly interface and so thin film cannot obviously prevent leakage, tunneling currents and boron diffusion (Morgen et al., 2006; Bahari et al., 2005; Morgen et al., 2005; Bahari et al., 2006, 2006b; Morgen et al., 2007; Bahari et al., 2008). The higher K- gate dielectric materials can thus be introduced as the alternative gate dielectrics for future of CMIS (I: insulator) devices.  $\text{La}_2\text{O}_3$  has largest band gap of the rare earth oxides at 4.3 eV, while also having the lowest lattice energy, with very high dielectric constant,  $\epsilon = 27$ . It is widely used in industry as well as in the research laboratory. Moreover, the  $\text{La}_2\text{O}_3/\text{CrO}_2$  gate stacks with high electrical permittivity show an amorphous structure of low temperature which can be used instead of ultrathin silicon dioxide gate dielectric in current CMOS devices (Duan et al., 2008; Alexazder et al., 2006; Dercz et al., 2006) due to its excellent chemical properties (Dercz et al., 2006; Zhu, 1998; Kurzweg et al., 1998; Betz et al., 1999) and independent  $\text{La}_2\text{O}_3$  network within the  $\text{CrO}_2$  network. However,  $\text{La}_2\text{O}_3$  has p-type semi-conducting properties because its resistivity decreases with an increase in temperature, average room temperature

resistivity is 10  $\text{k}\Omega\cdot\text{cm}$  (Kale et al., 2005).

In this work, we have synthesized  $\text{La}_2\text{O}_3/\text{CrO}_2$  which is suitable for CMIS. Different crystalline forms of lanthanum oxide have been prepared. At low temperatures,  $\text{La}_2\text{O}_3$  has an A- $\text{M}_2\text{O}_3$  hexagonal crystal structure (Kale et al., 2005). Its crystalline phase can be used for the potential applications of the ceramic – mesoporous structures, as an ingredient for the manufacture of piezoelectric and thermoelectric materials, automobile exhaust-gas converters contain  $\text{La}_2\text{O}_3$  (Cao et al., 2005).  $\text{La}_2\text{O}_3$  is also used in X-ray imaging intensifying screens, phosphors as well as dielectric and conductive ceramics. We have demonstrated to synthesis of hexagonal crystal phase (h- $\text{La}_2\text{O}_3$ ) at room temperature by using Sol-gel method. Some researchers (Wells, 1984; Wyckoff, 1963; Vinogradova et al., 2004; Manoilova, 2004) believe that the  $\text{La}^{3+}$  metal atoms are surrounded by a 7 coordinate group of  $\text{O}^{2-}$  atoms, while the oxygen ions are in an octahedral shape around the metal atom, we see there is one oxygen ion above one of the octahedral faces. In contrast to low temperature case, at high temperatures the  $\text{La}_2\text{O}_3$  converts to a C- $\text{M}_2\text{O}_3$  cubic crystal structure. The  $\text{La}^{3+}$  ion is surrounded by a 6 coordinate group of  $\text{O}^{2-}$  ions. However,  $\text{La}_2\text{O}_3$  in ferroelectric materials content has still needed to be studied due to its structural collapse during formation of the mesoporous phase and its phase transformation from hexagonal crystal phase

\*Corresponding author. E-mail: [a.bahari@umz.ac.ir](mailto:a.bahari@umz.ac.ir).



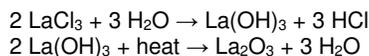
**Figure 1.** Preparation steps of  $\text{La}_2\text{O}_3$  powders. Similar procedure is for  $\text{CrO}_2$ .

to cubic crystal phase (Pajak et al., 2003; Duan et al., 2008; Alexazder et al., 2006; Dercz et al., 2006).

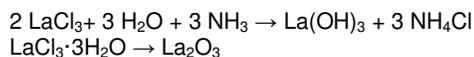
For this reason, we synthesize  $\text{CrO}_2$  nanoparticles in parallel to  $\text{La}_2\text{O}_3$  nanoparticles in this structure and the obtained results indicate the potential applications of the present combination.

### Experimental procedure and details

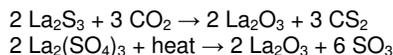
Lanthanum dioxide was prepared by the hydrolysis and condensation of  $\text{LaCl}_3$  used as precursor under acidic conditions. In this process, a 0.1 M solution of  $\text{LaCl}_3$  is sprayed onto a preheated substrate. We got two ways to control hydrolysis rate which can be viewed as occurring in hydrolysis followed by dehydration:



On the other hand, hexagonal  $\text{La}_2\text{O}_3$  involves precipitation of nominal  $\text{La}(\text{OH})_3$  from aqueous solution using a combination of 2.5%  $\text{NH}_3$  and the surfactant sodium dodecyl sulfate followed by heating and stirring for 24 h at  $80^\circ\text{C}$  (Vinogradova et al., 2004):



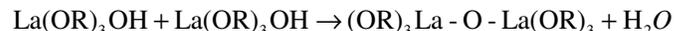
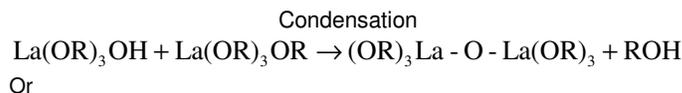
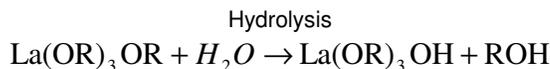
Other routes include:



Thus the kinetic is conditioned and it is becoming possible. The water amount necessary to the hydrolysis can be chemically controlled with the hydrolysis in order to decrease its reactivity. The precursor can then be hydrolyzed with a small amount of water produced *in situ* by an esterification reaction resulting of the two points: Depending on the pH of the compound, different crystal structures can be obtained.  $\text{La}_2\text{O}_3$  is hygroscopic; under atmosphere, lanthanum oxide absorbs moisture over time and converts to lanthanum hydroxide (Manoilova, 2004). It is worth noting that there are some reactions as well:



We have chosen the Sol-gel process to obtain a gel and privileging at maximum of connection formation  $\text{La}-\text{O}-\text{La}$ . The overall hydrolysis and condensation reactions are illustrated below:



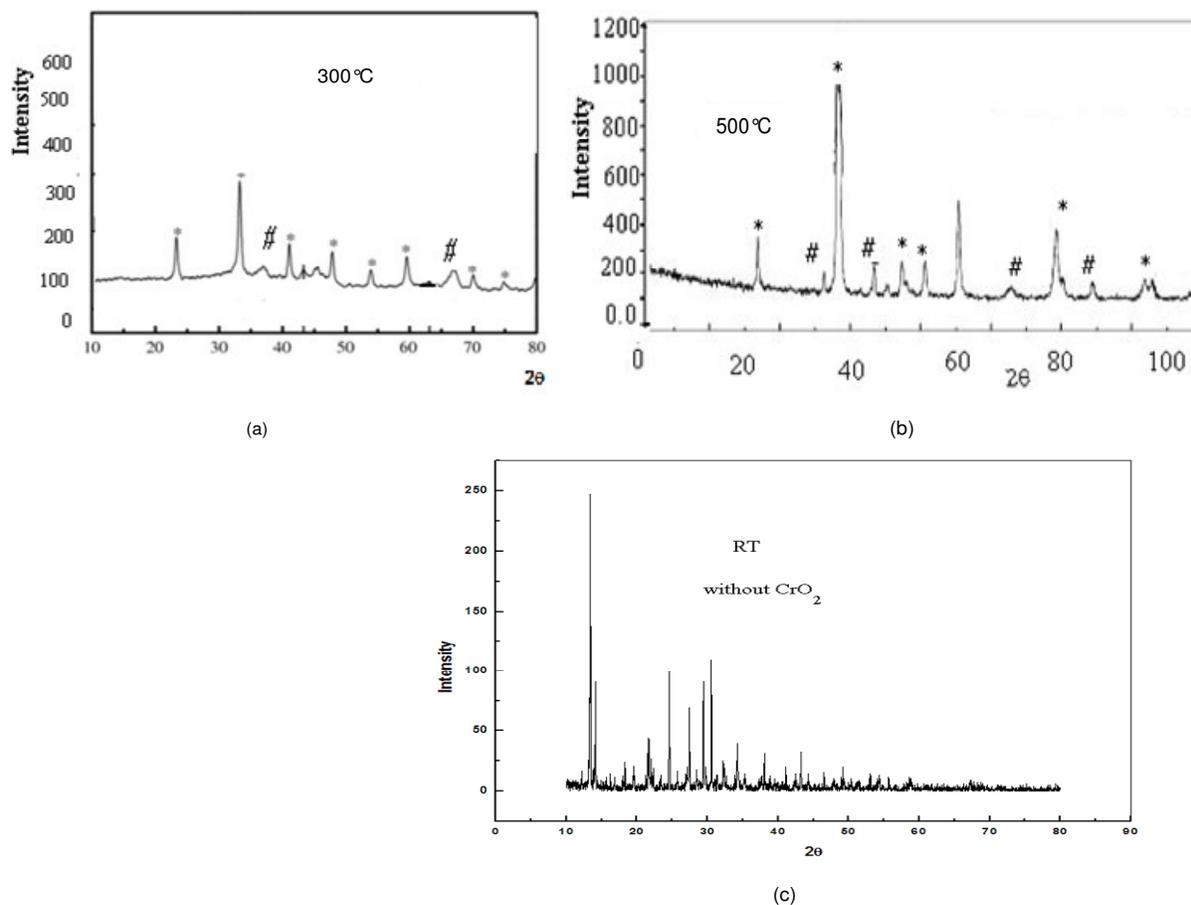
Where  $\text{OR} = \text{OC}_3\text{H}_7$ . The chemically controlled condensation of lanthanum alkoxide precursor leads to stable colloidal solutions of monodispersed lanthania nanoparticles.

The  $\text{La}_2\text{O}_3$  sol was prepared from a lanthanum alkoxide precursor (Betz et al., 1999; Kale et al., 2005; Cao et al., 2005; Wells, 1984; Wyckoff, 1963) lanthanum propoxide (Aldrich), acetic acid (sigma-aldrich) was used as a chelating agent to lanthanum propoxide and isopropanol (sigma-aldrich) as a solvent. To reduce the viscosity of the alkoxide and reactivity with moisture, the alkoxide solution was prepared by stirring lanthanum propoxide and isopropanol at room temperature in the molar ratio 1 La:15 isopropanol. Catalyst solution was with the molar composition of 1.0  $\text{H}_2\text{O}$ :0.6  $\text{HNO}_3$ :7.5 isopropanol was prepared using distilled water, nitric acid (sigma-Aldrich) and isopropanol. Acetic acid was added drop-wise to the stirred alkoxide solution until the molar ratio of acetic acid to La became 2.0, and the solution was kept stirring for 2 h to let complete the reaction between alkoxide and acetic acid. The catalyst solution was mixed with the aforementioned solution to produce a lanthania sol until the molar ratio of La: $\text{CH}_3\text{COOH}$ : $\text{HNO}_3$ : $\text{H}_2\text{O}$ : $\text{C}_3\text{H}_7\text{OH}$  became 1.0;2.0:1.2:2.0:30 and was then kept stirring for 2 h. The scheme of preparation is illustrated in Figure 1. Similarly, we can synthesize the nano scale  $\text{CrO}_2$  and add it into  $\text{La}_2\text{O}_3$  (Figures 2 and 3).

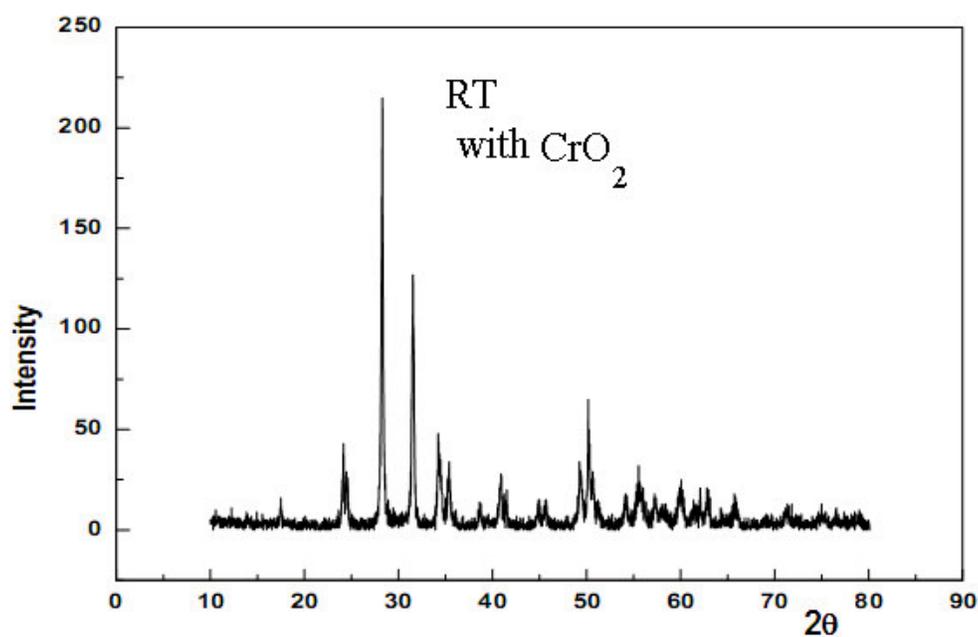
The properties of Lanthania forms of higher symmetry are very often preferable to cubic one.  $\text{CrO}_2$  is usually used as the stabilization component of higher symmetry lanthania (Betz et al., 1999; Cao et al., 2005; Wells, 1984; Wyckoff, 1963; Vinogradova et al., 2004; Manoilova, 2004). Figure 2 shows the XRD patterns of  $\text{La}_2\text{O}_3$  without  $\text{CrO}_2$ . As can be seen in Figure 2 (c) peaks at  $13^\circ$ ,  $24^\circ$ ,  $29$  to  $31^\circ$  and  $44^\circ$  attributed to the (111), (200), (220) and (311) diffraction planes of the hexagonal lanthania and some cubic lanthania peak at  $50$  to  $80^\circ\text{C}$ . Figure 3 displays the XRD pattern  $\text{La}_2\text{O}_3$  with  $\text{CrO}_2$  (the presence of  $\text{CrO}_2$  (50 wt%) in  $\text{La}_2\text{O}_3$ ). The new peaks in comparison to Figure 2, attributed to  $\text{CrO}_2$  phases. Phase beside of cubic, hexagonal of  $\text{La}_2\text{O}_3$  and cubic forms of  $\text{CrO}_2$  phase are stabilized. The size of nanoparticles is in the range from 20 to 60 nm as found with using x- powder method (Dercz et al., 2006; Zhu, 1998; Kurzweg et al., 1998; Betz et al., 1999; Kale et al., 2005; Cao et al., 2005) and shown in Figures 4 and 5. The amorphous structure is obtained at  $300^\circ\text{C}$  which can be used for gate dielectric of nano electronic devices. This amorphous structure has become to nano crystalline structure with heating the sample (Figure 2b,  $T = 500^\circ\text{C}$ ).

### Conclusion

Lanthanum oxide ( $\text{La}_2\text{O}_3$ ), also known as "lanthana" is usually supplied as an odourless white powder. It is



**Figure 2.** (a) The XRD pattern of nanoparticles at 300°C without CrO<sub>2</sub>. \* Indicates the hexagonal crystal phase and # shows cubic crystal phase. (b) The XRD pattern of nanoparticles at 500°C without CrO<sub>2</sub> and (c) The XRD pattern of nanoparticles at RT without CrO<sub>2</sub>.



**Figure 3.** The XRD pattern of nanoparticles at RT with CrO<sub>2</sub> (50% wt La<sub>2</sub>O<sub>3</sub> and 50% wt CrO<sub>2</sub>).

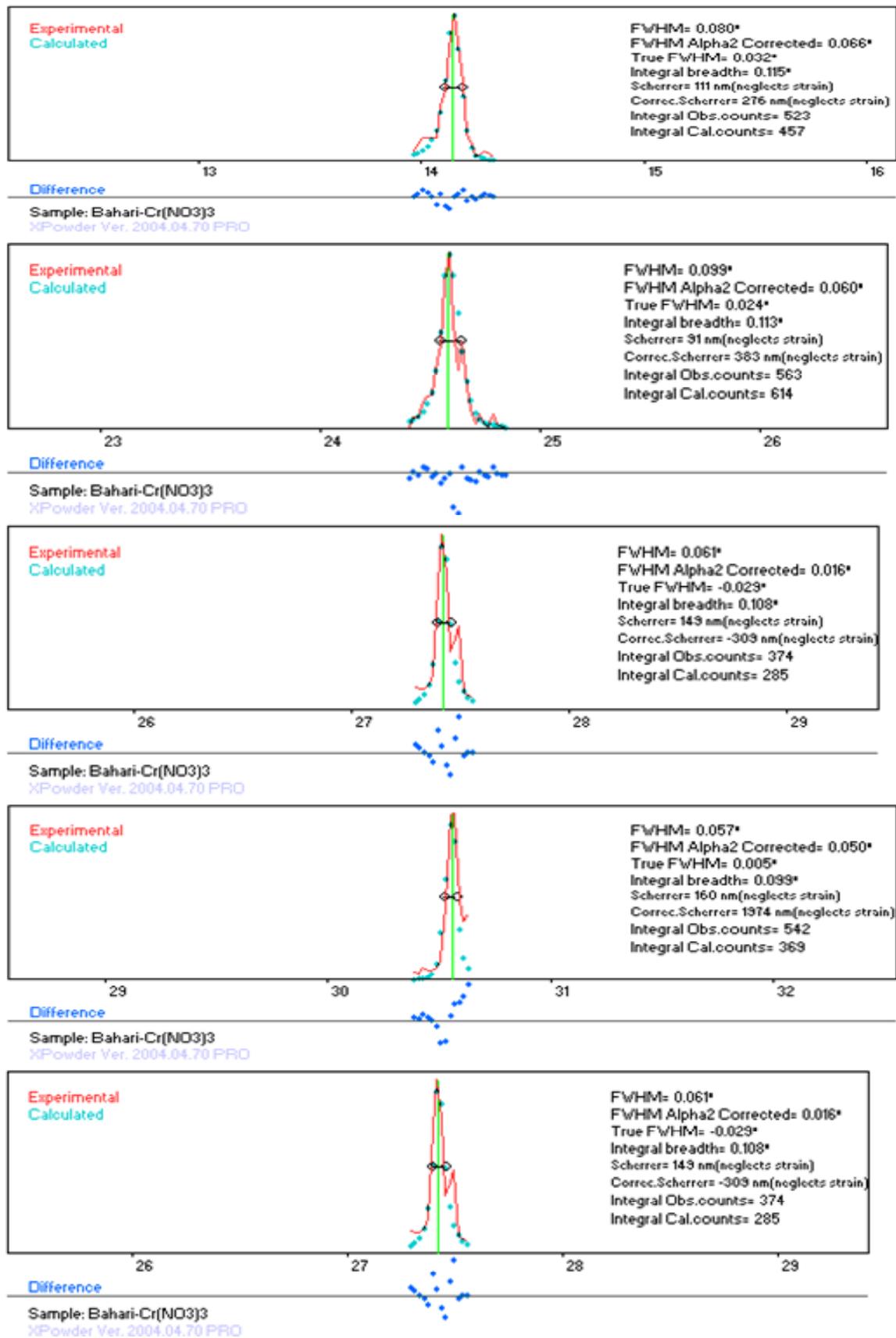
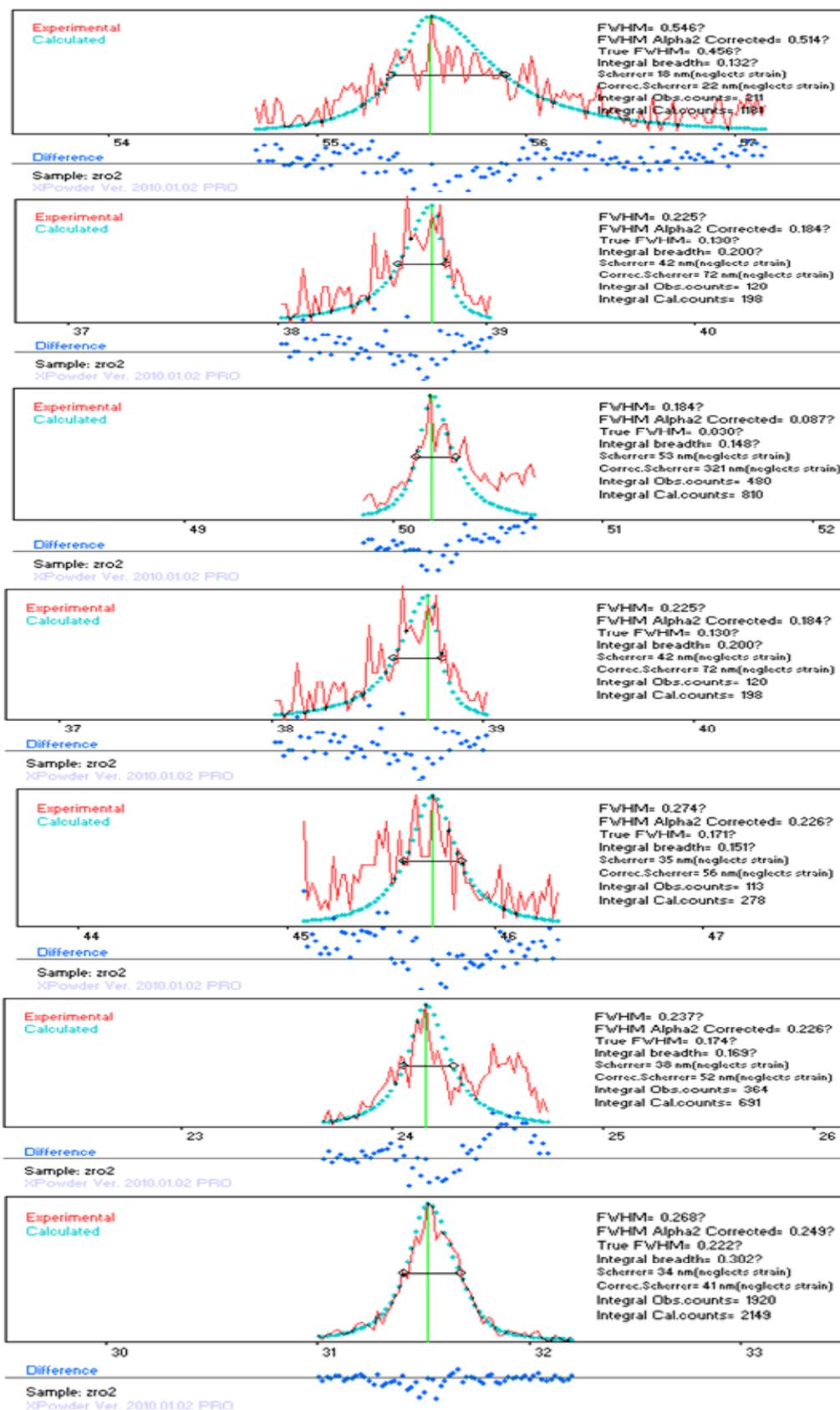


Figure 4. The size of nanoparticles correspond with Figure 2; and are determined using x- powder method.



**Figure 5.** The size of nanoparticles correspond with Figure 3; and are determined using x- powder method.

slightly soluble in water and soluble in acids.  $\text{La}_2\text{O}_3$  has been used to make optical glasses, to which this oxide confers increased density, refractive index and hardness.  $\text{La}_2\text{O}_3$  in  $\text{CrO}_2$  content have been synthesized at different temperatures. The fraction of the cubic  $\text{La}_2\text{O}_3$  decreases at low temperature, whilst it increases at  $500^\circ\text{C}$ . It means that we could get the progressive phase transformation from metastable hexagonal  $\text{La}_2\text{O}_3$  to stable cubic  $\text{La}_2\text{O}_3$  during heating. In the XRD patterns, one can see the presence of cubic, hexagonal of  $\text{La}_2\text{O}_3$  and cubic  $\text{CrO}_2$  phases. In this spectrum, the intensity cubic "lanthania" is so small component which indicates this phase is interoperated into "lanthania" phases. The peak broadening at  $500^\circ\text{C}$  (respect to room temperature) indicated the bigger size of the crystallites in the growth direction.

The amorphous structure of sample (at  $300^\circ\text{C}$ ) can be used as a good gate dielectric of nano electronic devices.

## REFERENCES

- Alexazder VI, Lyseuu SV, Baranova SV (2006). thermally stable materials based on mesostructured sulfated Lanthania. *Mesopor. Mater.*, 91: 254-2600.
- Alexazder VI, Lyseuu SV, Baranova SV (2006). Thermally stable materials based on mesostructured sulfated Lanthania, *Microporous Mesoporous Mater.*, 91: 254-2600.
- Bahari A, Morgen P, Li ZS (2008). Ultra thin silicon nitride films on Si(100) studied with core level photoemission. *Surf. Sci.*, 602: 2315-2324.
- Bahari A, Robenhagen U, Morgen P (2005). Growth of Ultra thin Silicon Nitride on Si(111) at low temperatures. *Phys. Rev. B.*, 72: 205323-205329.
- Morgen P, Bahari A, Rao MG, Li ZS (2005). Roads to Ultra thin Silicon Oxide. *J. Vacuum Technol. A.*, 23: 201-207.
- Bahari A, Morgen P, Li ZS, Pederson K (2006). Growth of a Stacked Silicon Nitride /Silicon Oxide Dielectric on Si (100). *J. Vacuum Sci. Technol.*, 24: 2119-2123.
- Bahari A, Morgen P, Li ZS (2006). Valence Band Studies of the Formation Ultra thin Pure Silicon Nitride Films on Si(100). *Surf. Sci.*, 600: 2966-2971.
- Betz U, Sturm A, Loeffler JF, Wagner W, Wiedenmann A, Hahn H (1999). Low-temperature isothermal sintering and microstructural characterization of nanocrystalline Lanthania ceramics using small angle neutron scattering. *NanoStruct. Mater.*, 12: 689-692.
- Cao J, Liu H, Zheng M, Chang X, Ma X, Zhang A, Xu Q (2005). Controllable syntheses of hexagonal and lamellar mesostructured lanthanum oxide. *Mater. Lett.*, 59: 408-416.
- Duan G, Zhang C, Li A, Yang X, Lu L, Wang X (2008). Preparation and characterization of mesoporous Lanthania made by using a poly (methyl methacrylate) tamplate. *Nanoscale Res. Lett.*, 3: 118-122.
- Dercz G, Prusik K, Pajak L (2006). Structure investigations of commercial Lanthania ceramic powder, *J. Achiev. Mater. Manuf. Eng.*, 18: 259-262.
- Duan G, Zhang C, Li A, Yang X, Lu L, Wang X (2008). Preparation and characterization of mesoporous Lanthania made by using a poly (methyl methacrylate) tamplate. *Nanoscale Res. Lett.*, 3: 118-122.
- Kale S, Jadhav K, Patil P, Gujar T, Lokhande C (2005). Characterizations of spray-deposited Lanthanum oxide ( $\text{La}_2\text{O}_3$ ) thin films. *Mater. Lett.*, 59: 3007-3024.
- Kurzweg W, Heimann RB, Troczynski T, Waymann ML (1998). Development of plasma sprayed bioceramic coatings with bond coats based on Titania and Lanthania. *Bomaterials*, 19: 1507-1511.
- Manoilova OV (2004). Surface Acidity and Basicity of  $\text{La}_2\text{O}_3$ ,  $\text{LaOCl}$ , and  $\text{LaCl}_3$  Characterized by IR Spectroscopy, TPD, and DFT Calculations. *J. Phys. Chem. B.*, 108: 15770-15776.
- Morgen P, Bahari AP (2006). Functional properties of Nano structured Material. Springer, pp. 229-257.
- Morgen P, Bahari A, Pedersen K, Li Z (2007). Plasma assisted growth of ultra thin nitrides on Si surfaces under ultra high vacuum conditions. *J. Phys.*, 86: 12019-12038.
- Pajak L, Formanek B, Dercz G (2003). Dispersion analysis of NiAl-TiC- $\text{Al}_2\text{O}_3$  composite powder. Proceedings of 12<sup>th</sup> Scientific International Conference. *Achiev. Mech. Mater. Eng. AMME'2003, Gliwice-Zakopane*, pp. 723-726.
- Vinogradova N, Dmitruk L, Petrova O (2004). Glass Transition and Crystallization of Glasses Based on Rare-Earth Borates. *Glass Phys. Chem.*, 30: 1-15.
- Wells AF (1984). *Structural Inorganic Chemistry*. Oxford: Clarendon Press, p. 546.
- Wyckoff RWG (1963). *Crystal Structures: Inorganic Compounds  $\text{RX}_n$ ,  $\text{RnMX}_2$ ,  $\text{RnMX}_3$* . New York: Interscience Publishers.
- Zhu WZ (1998). Effect of Cubic Phase on the Kinetics of the Isothermal Hexagonal to Cubic Transformation in  $\text{La}_2\text{O}_3$  (3 mol% $\text{Y}_2\text{O}_3$ ) Ceramics. *Ceram. Int.*, 24: 35-43.